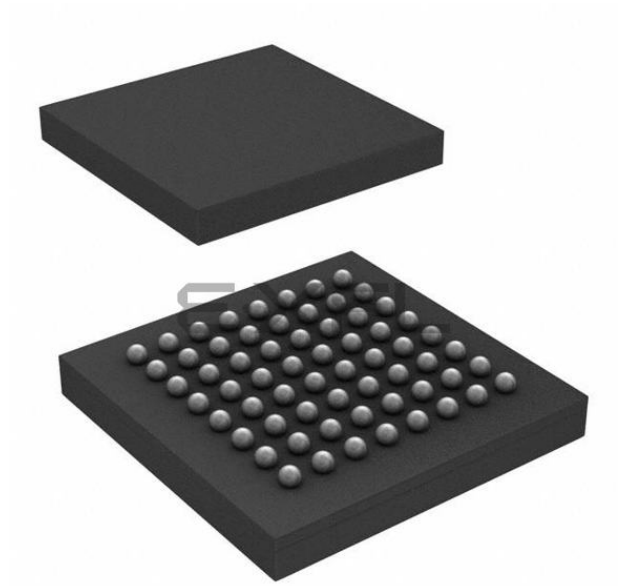

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-UFBGA, WLCSP
Supplier Device Package	64-WLCSP (3.36x3.66)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l451rcy6tr

- **Shutdown** mode

  The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the V_{CORE} domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

  The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

  The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

  SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

  The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

  The system clock after wakeup is MSI at 4 MHz.

Figure 4. Clock tree

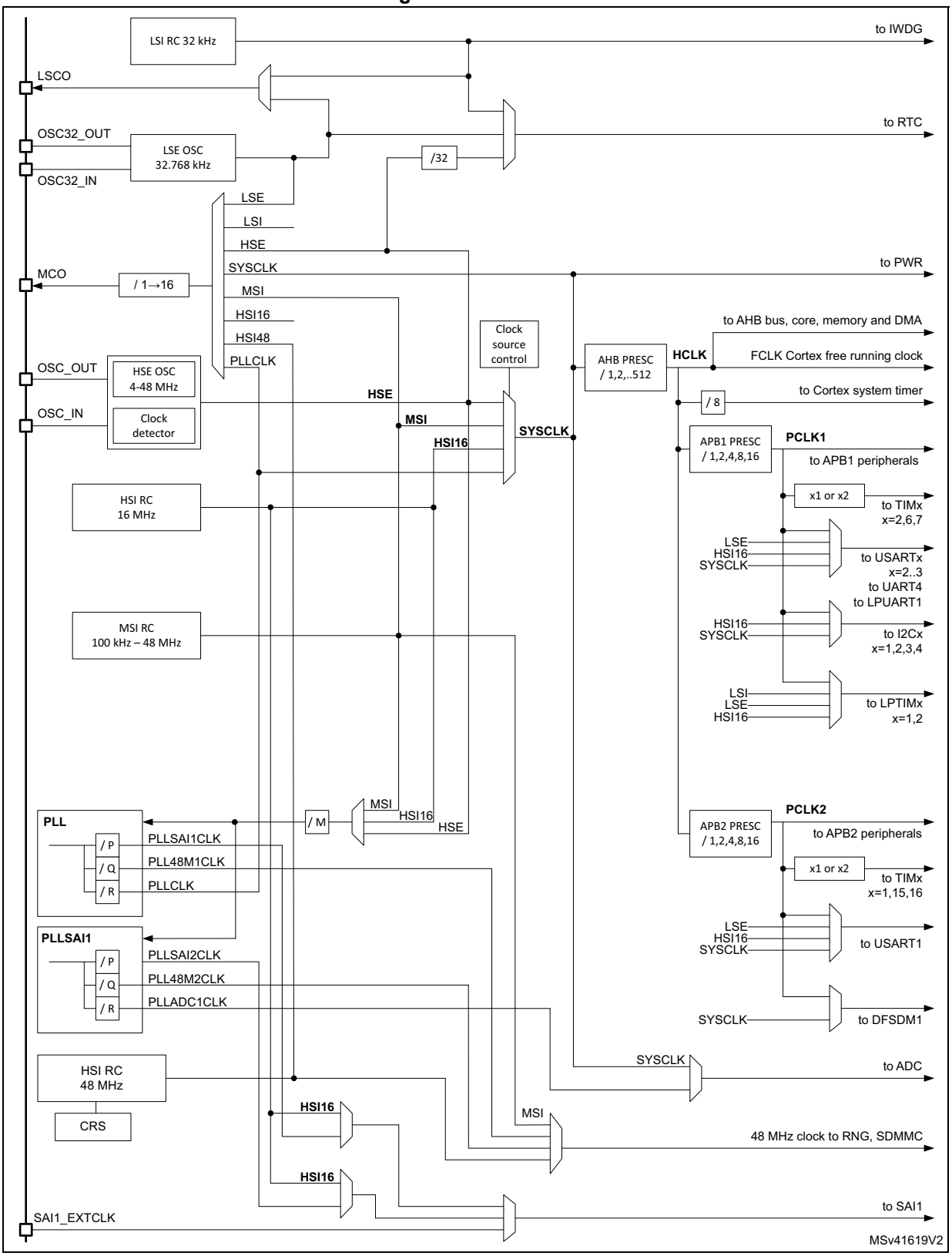
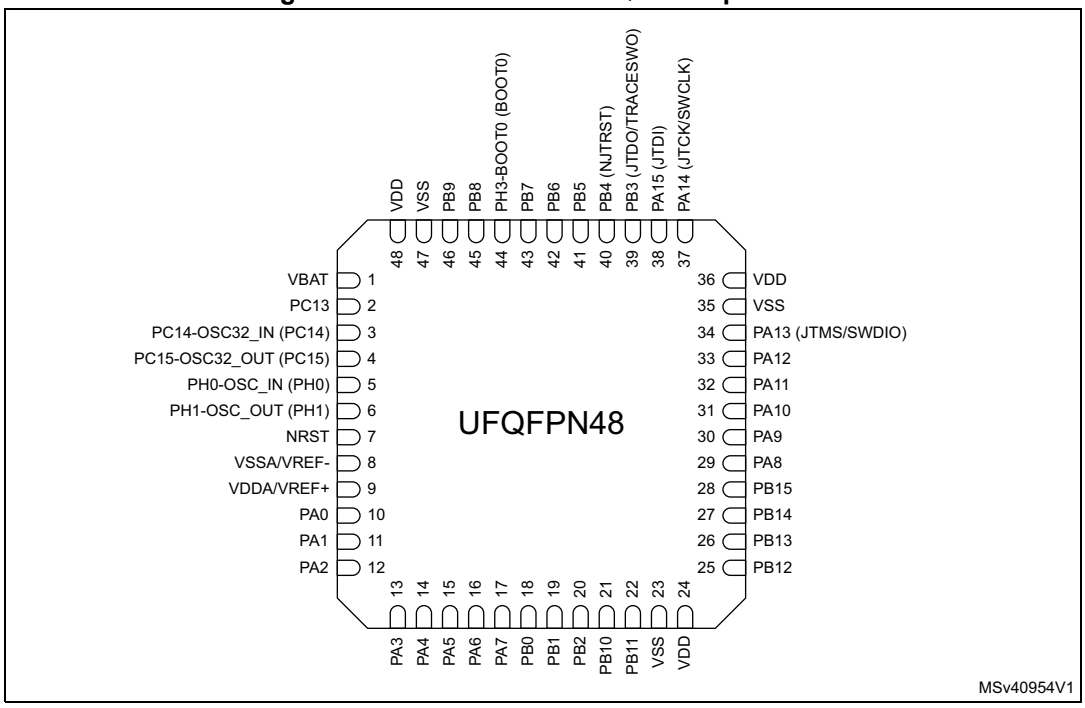


Figure 11. STM32L451Cx UFQFPN48 pinout(1)



1. The above figure shows the package top view.

Table 15. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		TT	3.6 V tolerant I/O
		RST	Bidirectional reset pin with embedded weak pull-up resistor
		Option for TT or FT I/Os	
		_f (1)	I/O, Fm+ capable
		_a (2)	I/O, with Analog switch function supplied by V_{DDA}
Notes		Unless otherwise specified by a note, all I/Os are set as analog inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

1. The related I/O structures in *Table 16* are: FT_f, FT_fa.
2. The related I/O structures in *Table 16* are: FT_a, FT_fa, TT_a.

Table 17. Alternate function AF0 to AF7[1] (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2 LPTIM1	I2C4/TIM1/ TIM2/TIM3	I2C4/USART2/ CAN1/TIM1	I2C1/I2C2/ I2C3/I2C4	SPI1/SPI2/I2C4	SPI3/DFSDM/ COMP1	USART1/ USART2/ USART3
Port H	PH0	-	-	-	-	-	-	-	-
	PH1	-	-	-	-	-	-	-	-
	PH3	-	-	-	-	-	-	-	-

1. Please refer to *Table 18* for AF8 to AF15.

Table 18. Alternate function AF8 to AF15[1] (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/ LPUART1/ CAN1	CAN1/TSC	CAN1/ QUADSPI	-	SDMMC1/ COMP1/ COMP2	SAI1	TIM2/TIM15/ TIM16/LPTIM2	EVENTOUT
Port C	PC0	LPUART1_RX	-	-	-	-	-	LPTIM2_IN1	EVENTOUT
	PC1	LPUART1_TX	-	-	-	-	-	-	EVENTOUT
	PC2	-	-	-	-	-	-	-	EVENTOUT
	PC3	-	-	-	-	-	SAI1_SD_A	LPTIM2_ETR	EVENTOUT
	PC4	-	-	-	-	-	-	-	EVENTOUT
	PC5	-	-	-	-	-	-	-	EVENTOUT
	PC6	-	TSC_G4_IO1	-	-	SDMMC1_D6	-	-	EVENTOUT
	PC7	-	TSC_G4_IO2	-	-	SDMMC1_D7	-	-	EVENTOUT
	PC8	-	TSC_G4_IO3	-	-	SDMMC1_D0	-	-	EVENTOUT
	PC9	-	TSC_G4_IO4	-	-	SDMMC1_D1	-	-	EVENTOUT
	PC10	UART4_TX	TSC_G3_IO2	-	-	SDMMC1_D2	-	-	EVENTOUT
	PC11	UART4_RX	TSC_G3_IO3	-	-	SDMMC1_D3	-	-	EVENTOUT
	PC12	-	TSC_G3_IO4	-	-	SDMMC1_CK	-	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	EVENTOUT
	PC15	-	-	-	-	-	-	-	EVENTOUT

Table 18. Alternate function AF8 to AF15[1] (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/ LPUART1/ CAN1	CAN1/TSC	CAN1/ QUADSPI	-	SDMMC1/ COMP1/ COMP2	SAI1	TIM2/TIM15/ TIM16/LPTIM2	EVENTOUT
Port E	PE0	-	-	-	-	-	-	TIM16_CH1	EVENTOUT
	PE1	-	-	-	-	-	-	-	EVENTOUT
	PE2	-	TSC_G7_IO1	-	-	-	SAI1_MCLK_A	-	EVENTOUT
	PE3	-	TSC_G7_IO2	-	-	-	SAI1_SD_B	-	EVENTOUT
	PE4	-	TSC_G7_IO3	-	-	-	SAI1_FS_A	-	EVENTOUT
	PE5	-	TSC_G7_IO4	-	-	-	SAI1_SCK_A	-	EVENTOUT
	PE6	-	-	-	-	-	SAI1_SD_A	-	EVENTOUT
	PE7	-	-	-	-	-	SAI1_SD_B	-	EVENTOUT
	PE8	-	-	-	-	-	SAI1_SCK_B	-	EVENTOUT
	PE9	-	-	-	-	-	SAI1_FS_B	-	EVENTOUT
	PE10	-	TSC_G5_IO1	QUADSPI_CLK	-	-	SAI1_MCLK_B	-	EVENTOUT
	PE11	-	TSC_G5_IO2	QUADSPI_ BK1_NCS	-	-	-	-	EVENTOUT
	PE12	-	TSC_G5_IO3	QUADSPI_ BK1_IO0	-	-	-	-	EVENTOUT
	PE13	-	TSC_G5_IO4	QUADSPI_ BK1_IO1	-	-	-	-	EVENTOUT
	PE14	-	-	QUADSPI_ BK1_IO2	-	-	-	-	EVENTOUT
	PE15	-	-	QUADSPI_ BK1_IO3	-	-	-	-	EVENTOUT
Port H	PH0	-	-	-	-	-	-	-	EVENTOUT
	PH1	-	-	-	-	-	-	-	EVENTOUT
	PH3	-	-	-	-	-	-	-	EVENTOUT

Table 25. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
V_{PVD0}	Programmable voltage detector threshold 0	Rising edge	2.1	2.15	2.19	V
		Falling edge	2	2.05	2.1	
V_{PVD1}	PVD threshold 1	Rising edge	2.26	2.31	2.36	V
		Falling edge	2.15	2.20	2.25	
V_{PVD2}	PVD threshold 2	Rising edge	2.41	2.46	2.51	V
		Falling edge	2.31	2.36	2.41	
V_{PVD3}	PVD threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{PVD4}	PVD threshold 4	Rising edge	2.69	2.74	2.79	V
		Falling edge	2.59	2.64	2.69	
V_{PVD5}	PVD threshold 5	Rising edge	2.85	2.91	2.96	V
		Falling edge	2.75	2.81	2.86	
V_{PVD6}	PVD threshold 6	Rising edge	2.92	2.98	3.04	V
		Falling edge	2.84	2.90	2.96	
V_{hyst_BORH0}	Hysteresis voltage of BORH0	Hysteresis in continuous mode	-	20	-	mV
		Hysteresis in other mode	-	30	-	
$V_{hyst\_BOR\_PVD}$	Hysteresis voltage of BORH (except BORH0) and PVD	-	-	100	-	mV
I_{DD} (BOR_PVD)[2]	BOR[3] (except BOR0) and PVD consumption from V_{DD}	-	-	1.1	1.6	µA
V_{PVM3}	V_{DDA} peripheral voltage monitoring	Rising edge	1.61	1.65	1.69	V
		Falling edge	1.6	1.64	1.68	
V_{PVM4}	V_{DDA} peripheral voltage monitoring	Rising edge	1.78	1.82	1.86	V
		Falling edge	1.77	1.81	1.85	
V_{hyst_PVM3}	PVM3 hysteresis	-	-	10	-	mV
V_{hyst_PVM4}	PVM4 hysteresis	-	-	10	-	mV
I_{DD} (PVM1) (2)	PVM1 consumption from V_{DD}	-	-	0.2	-	µA
I_{DD} (PVM3/PVM4) (2)	PVM3 and PVM4 consumption from V_{DD}	-	-	2	-	µA

1. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.
2. Guaranteed by design.
3. BOR0 is enabled in all modes (except shutdown) and its consumption is therefore included in the supply current characteristics tables.

Table 33. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Sleep)	Supply current in sleep mode,	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.700	0.730	0.830	1.00	1.35	0.80	0.90	1.05	1.30	1.90	mA
				16 MHz	0.475	0.505	0.605	0.775	1.10	0.55	0.65	0.80	1.05	1.65	
				8 MHz	0.300	0.325	0.425	0.590	0.920	0.35	0.45	0.60	0.85	1.45	
				4 MHz	0.210	0.235	0.335	0.500	0.830	0.25	0.30	0.45	0.75	1.35	
				2 MHz	0.165	0.190	0.290	0.455	0.785	0.20	0.25	0.40	0.70	1.25	
				1 MHz	0.145	0.170	0.265	0.430	0.760	0.15	0.25	0.40	0.65	1.25	
				100 kHz	0.125	0.150	0.245	0.410	0.740	0.15	0.20	0.35	0.65	1.20	
			Range 1	80 MHz	2.30	2.35	2.45	2.65	3.05	2.55	2.65	2.85	3.15	3.80	
				72 MHz	2.10	2.15	2.25	2.45	2.80	2.35	2.40	2.60	2.90	3.55	
				64 MHz	1.90	1.90	2.05	2.25	2.60	2.10	2.20	2.35	2.70	3.35	
				48 MHz	1.40	1.40	1.55	1.75	2.15	1.60	1.65	1.85	2.15	2.80	
				32 MHz	0.970	1.00	1.15	1.30	1.70	1.10	1.20	1.40	1.70	2.35	
				24 MHz	0.765	0.800	0.920	1.10	1.50	0.90	0.95	1.15	1.45	2.10	
				16 MHz	0.555	0.590	0.705	0.895	1.25	0.65	0.75	0.90	1.20	1.85	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	76.0	110	215	395	745	120	185	355	610	1250	µA
				1 MHz	54.0	86.5	195	370	725	88.5	160	335	585	1250	
				400 kHz	39.0	70.5	175	355	710	68.5	140	320	570	1200	
				100 kHz	35.5	75.0	195	345	715	66.0	130	305	560	1200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 34. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	76.5	105	220	410	740	110	175	350	600	1250	µA
				1 MHz	54.0	81.0	195	385	715	81.5	155	325	570	1200	
				400 kHz	28.0	64.5	175	370	695	60.5	130	305	555	1200	
				100 kHz	21.5	55.0	170	360	690	58.5	120	300	550	1200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 35. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	-	1.8 V	2.05	5.40	19.0	44.0	97.0	4.00	11.5	41.5	100	220	µA
			2.4 V	2.10	5.45	19.0	44.5	98.5	4.05	11.5	42.0	100	225	
			3 V	2.05	5.55	19.5	45.0	100	4.10	12.0	43.0	105	230	
			3.6 V	2.05	5.65	20.0	46.5	105	4.20	12.0	44.0	105	235	
I_{DD_ALL} (Stop 2 with RTC)	Supply current in Stop 2 mode, RTC enabled	RTC clocked by LSI	1.8 V	2.30	5.65	19.0	44.0	97.0	4.50	12.0	42.0	100	220	µA
			2.4 V	2.35	5.80	19.5	44.5	99.0	4.65	12.0	42.5	100	225	
			3 V	2.50	5.90	20.0	45.5	100	4.90	12.5	43.5	105	230	
			3.6 V	2.60	6.15	20.5	47.0	105	5.20	13.0	44.5	105	235	
		RTC clocked by LSE bypassed at 32768 Hz	1.8 V	2.60	6.05	21.0	48.0	97.0	-	-	-	-	-	
			2.4 V	2.55	6.20	21.0	49.0	98.5	-	-	-	-	-	
			3 V	2.80	6.35	21.5	49.5	100	-	-	-	-	-	
			3.6 V	2.85	6.60	22.5	51.5	105	-	-	-	-	-	
		RTC clocked by LSE quartz(2) in low drive mode	1.8 V	2.40	5.70	19.0	44.5	98.0	-	-	-	-	-	
			2.4 V	2.50	5.85	19.5	45.0	99.5	-	-	-	-	-	
			3 V	2.60	6.00	20.0	46.0	100	-	-	-	-	-	
			3.6 V	2.65	6.25	20.5	47.0	105	-	-	-	-	-	

Table 39. Current consumption in Shutdown mode (continued)

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Shutdown with RTC)	Supply current in Shutdown mode (backup registers retained) RTC enabled	RTC clocked by LSE bypassed at 32768 Hz	1.8 V	165	275	950	2600	6550	-	-	-	-	-	nA
			2.4 V	235	370	1150	3100	7650	-	-	-	-	-	
			3 V	325	485	1450	3750	9050	-	-	-	-	-	
			3.6 V	445	655	1900	4800	11500	-	-	-	-	-	
		RTC clocked by LSE quartz (2) in low drive mode	1.8 V	290	410	1050	2550	6700	-	-	-	-	-	
			2.4 V	375	515	1250	3050	7800	-	-	-	-	-	
			3 V	480	645	1550	3700	8800	-	-	-	-	-	
			3.6 V	625	840	1950	4950	11500	-	-	-	-	-	
I_{DD_ALL} (wakeup from Shutdown)	Supply current during wakeup from Shutdown mode	Wakeup clock is MSI = 4 MHz. See (3).	3 V	1.00	-	-	-	-	-	-	-	-	-	mA

1. Guaranteed by characterization results, unless otherwise specified.
2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
3. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in *Table 42: Low-power mode wakeup timings*.

Table 40. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{BAT}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_VBAT} (VBAT)	Backup domain supply current	RTC disabled	1.8 V	3.00	-	-	-	-	-	-	-	-	-	nA
			2.4 V	4.00	-	-	-	-	-	-	-	-	-	
			3 V	5.00	-	-	-	-	-	-	-	-	-	
			3.6 V	11.0	-	-	-	-	-	-	-	-	-	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	145	165	285	550	-	-	-	-	-	-	
			2.4 V	205	235	370	670	-	-	-	-	-	-	
			3 V	285	315	470	820	-	-	-	-	-	-	
			3.6 V	375	430	715	1350	-	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

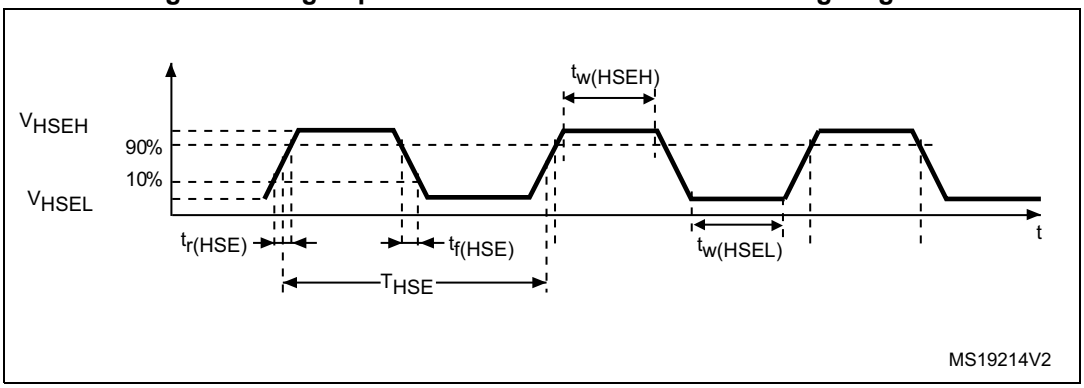
The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 18: High-speed external clock source AC timing diagram*.

Table 45. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	Voltage scaling Range 1	-	8	48	MHz
		Voltage scaling Range 2	-	8	26	
V_{HSEH}	OSC_IN input pin high level voltage	-	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	0.3 V_{DDIOx}	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time	Voltage scaling Range 1	7	-	-	ns
		Voltage scaling Range 2	18	-	-	

1. Guaranteed by design.

Figure 18. High-speed external clock source AC timing diagram



6.3.10 Flash memory characteristics

Table 54. Flash memory characteristics(1)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{prog}	64-bit programming time	-	81.69	90.76	µs
t_{prog_row}	one row (32 double word) programming time	normal programming	2.61	2.90	ms
		fast programming	1.91	2.12	
t_{prog_page}	one page (2 Kbyte) programming time	normal programming	20.91	23.24	
		fast programming	15.29	16.98	
t_{ERASE}	Page (2 KB) erase time	-	22.02	24.47	
t_{prog_bank}	one bank (512 Kbyte) programming time	normal programming	5.35	5.95	s
		fast programming	3.91	4.35	
t_{ME}	Mass erase time (one or two banks)	-	22.13	24.59	ms
I_{DD}	Average consumption from V_{DD}	Write mode	3.4	-	mA
		Erase mode	3.4	-	
	Maximum current (peak)	Write mode	7 (for 2 µs)	-	
		Erase mode	7 (for 41 µs)	-	

1. Guaranteed by design.

Table 55. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	15	
		1 kcycle(2) at T_A = 125 °C	7	
		10 kcycles(2) at T_A = 55 °C	30	
		10 kcycles(2) at T_A = 85 °C	15	
		10 kcycles(2) at T_A = 105 °C	10	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 57. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8 MHz/ 80 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	-8	dBµV
			30 MHz to 130 MHz	2	
			130 MHz to 1 GHz	5	
			1 GHz to 2 GHz	8	
			EMI Level	2.5	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 58. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	C3	250	

1. Guaranteed by characterization results.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DDIOx,}$ plus the maximum consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 20: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 20: Voltage characteristics*).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT OR TT unless otherwise specified).

Table 62. Output voltage characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		V_{DDIOx}-0.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	TTL port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	
V_{OH}(3)	Output high level voltage for an I/O pin		2.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}-1.3	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 4 mA $V_{DDIOx} \geq 1.62$ V	-	0.45	
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}-0.45	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 2 mA 1.62 V ≥ V_{DDIOx} ≥ 1.08 V	-	$0.35_x V_{DDIOx}$	
V_{OH}(3)	Output high level voltage for an I/O pin		$0.65_x V_{DDIOx}$	-	
V_{OLFM+}(3)	Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with "f" option)	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	
		$\|I_{IO}\|$ = 10 mA $V_{DDIOx} \geq 1.62$ V	-	0.4	
		$\|I_{IO}\|$ = 2 mA 1.62 V ≥ V_{DDIOx} ≥ 1.08 V	-	0.4	

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 20: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Guaranteed by design.

Input/output AC characteristics

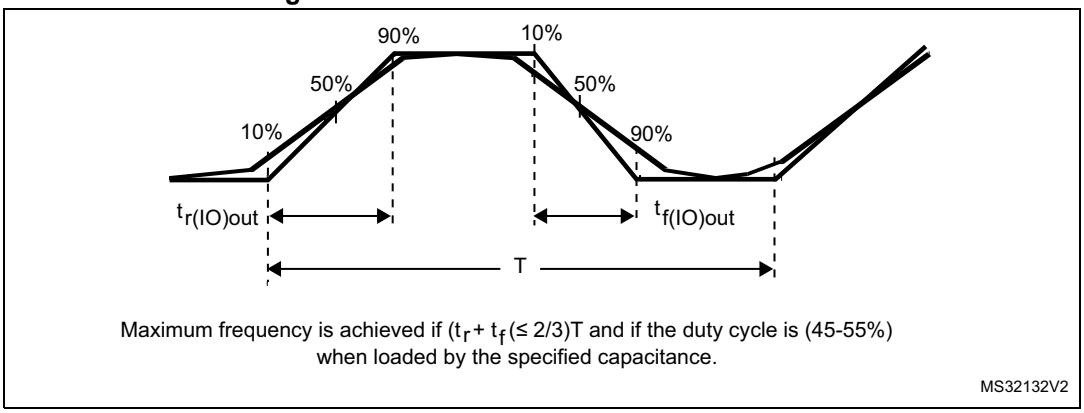
The definition and values of input/output AC characteristics are given in *Figure 26* and *Table 63*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Table 63. I/O AC characteristics(1)(2)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	10	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	52	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	140	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	17	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	10	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	15	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	9	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	16	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	40	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	4.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	9	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	21	

Figure 26. I/O AC characteristics definition(1)



1. Refer to *Table 63: I/O AC characteristics*.

6.3.15 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, R_{PU}.

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Table 64. NRST pin characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$	NRST input low level voltage	-	-	-	$0.3 \times V_{DDIOx}$	V
$V_{IH(NRST)}$	NRST input high level voltage	-	$0.7 \times V_{DDIOx}$	-	-	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	25	40	55	kΩ
$V_{F(NRST)}$	NRST input filtered pulse	-	-	-	70	ns
$V_{NF(NRST)}$	NRST input not filtered pulse	1.71 V ≤ V_{DD} ≤ 3.6 V	350	-	-	ns

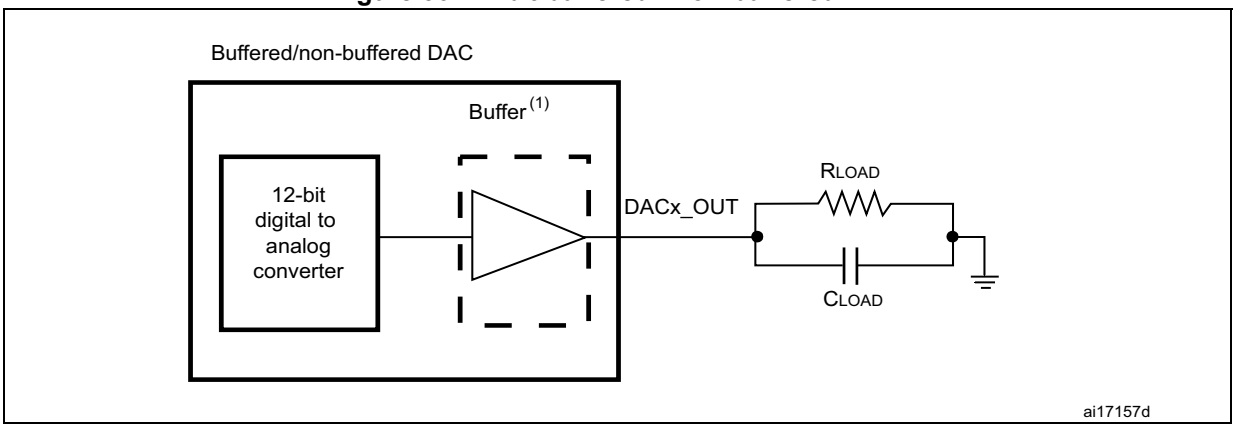
1. Guaranteed by design.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

Table 73. DAC characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{DDV}(DAC)	DAC consumption from V_{REF+}	DAC output buffer ON	No load, middle code (0x800)	-	185	240	µA
			No load, worst code (0xF1C)	-	340	400	
		DAC output buffer OFF	No load, middle code (0x800)	-	155	205	
		Sample and hold mode, buffer ON, C_{SH} = 100 nF, worst case		-	185 x Ton/(Ton +Toff) (4)	400 x Ton/(Ton +Toff) (4)	
		Sample and hold mode, buffer OFF, C_{SH} = 100 nF, worst case		-	155 x Ton/(Ton +Toff) (4)	205 x Ton/(Ton +Toff) (4)	

1. Guaranteed by design.
2. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).
3. Refer to *Table 61: I/O static characteristics*.
4. Ton is the Refresh phase duration. Toff is the Hold phase duration. Refer to RM0394 reference manual for more details.

Figure 30. 12-bit buffered / non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

Table 76. COMP characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{DDA}(COMP)	Comparator consumption from V_{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	1200	-	
		Medium mode	Static	-	5	7	µA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	
I_{bias}	Comparator input bias current	-		-	-	-(4)	nA

1. Guaranteed by design, unless otherwise specified.
2. Refer to *Table 26: Embedded internal voltage reference*.
3. Guaranteed by characterization results.
4. Mostly I/O leakage when used in analog mode. Refer to I_{lkg} parameter in *Table 61: I/O static characteristics*.

6.3.22 Operational amplifiers characteristics

Table 77. OPAMP characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage(2)	-	1.8	-	3.6	V
CMIR	Common mode input range	-	0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	25 °C, No Load on output.	-	-	±1.5	mV
		All voltage/Temp.	-	-	±3	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode	-	±5	-	µV/°C
		Low-power mode	-	±10	-	
TRIMOFFSETP TRIMLPOFFSETP	Offset trim step at low common input voltage (0.1 x V_{DDA})	-	-	0.8	1.1	mV
TRIMOFFSETN TRIMLPOFFSETN	Offset trim step at high common input voltage (0.9 x V_{DDA})	-	-	1	1.35	

Table 96. UFBGA64 recommended PCB design rules (0.5 mm pitch BGA) (continued)

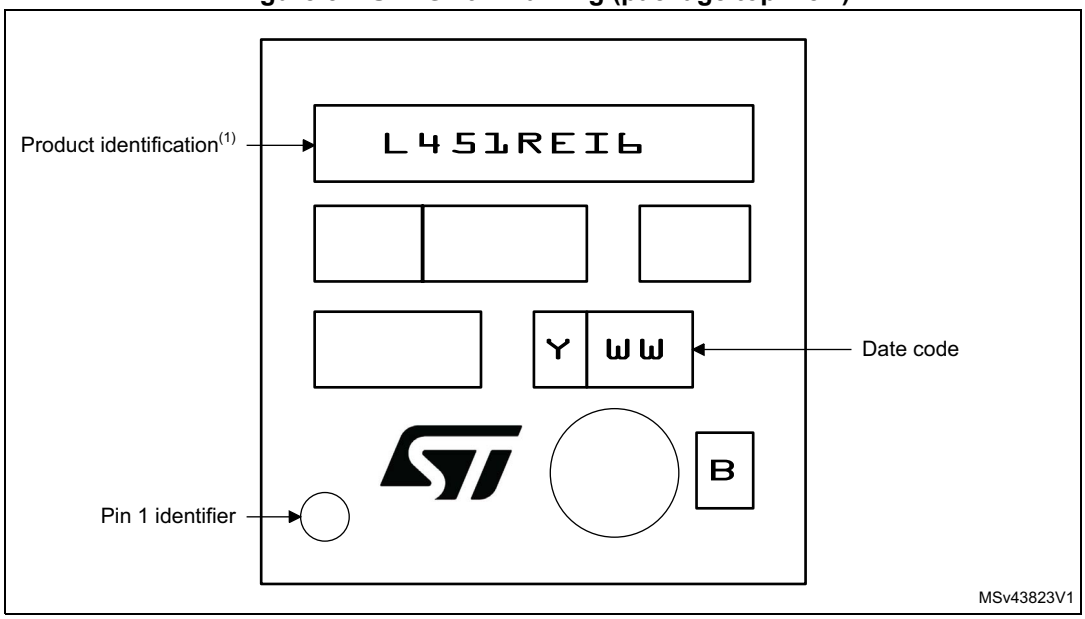
Dimension	Recommended values
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 51. UFBGA64 marking (package top view)



1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 75 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Using the values obtained in *Table 100* T_{Jmax} is calculated as follows:

– For LQFP64, 58 °C/W

T_{Jmax} = 75 °C + (58 °C/W × 447 mW) = 75 °C + 25.926 °C = 100.926 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C) see *Section 8: Ordering information*.

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 3).

Suffix 6: T_{Amax} = T_{Jmax} - (58°C/W × 447 mW) = 105-25.926 = 79.074 °C

Suffix 3: T_{Amax} = T_{Jmax} - (58°C/W × 447 mW) = 130-25.926 = 104.074 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 100 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

Using the values obtained in *Table 100* T_{Jmax} is calculated as follows:

– For LQFP64, 58 °C/W

T_{Jmax} = 100 °C + (58 °C/W × 134 mW) = 100 °C + 7.772 °C = 107.772 °C

This is above the range of the suffix 6 version parts (–40 < T_J < 105 °C).